

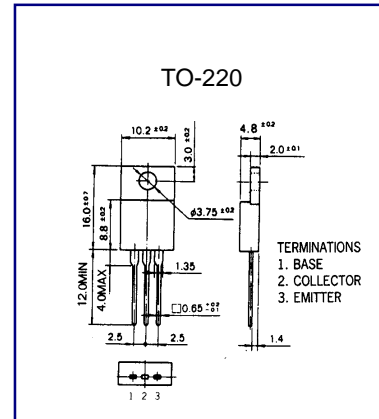


2SD288

NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

*



ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	8.0	V
Collector-Emitter Voltage	V _{CE0}	55	V
Emitter-Base voltage	V _{EB0}	5	V
Collector Current (DC)	I _C	3	A
Collector Dissipation (T _c =25°C)	P _C	20	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 50V , I _E =0			50	μA
DC Current Gain	h _{FE1}	V _{CE} = 5V , I _C =0.5A	40		240	V
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =1A , I _B =0.1A			1.0	
Current Gain Bandwidth Product						

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.